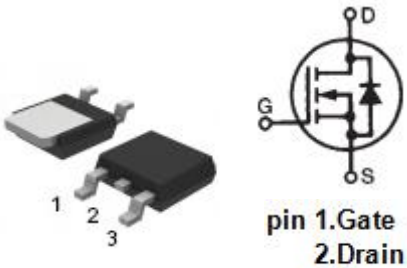
isc N-Channel MOSFET Transistor RD3T100CN

FEATURES

- Drain Current –I_D= 10A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= 200V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ = 182mΩ (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



DESCRIPTION

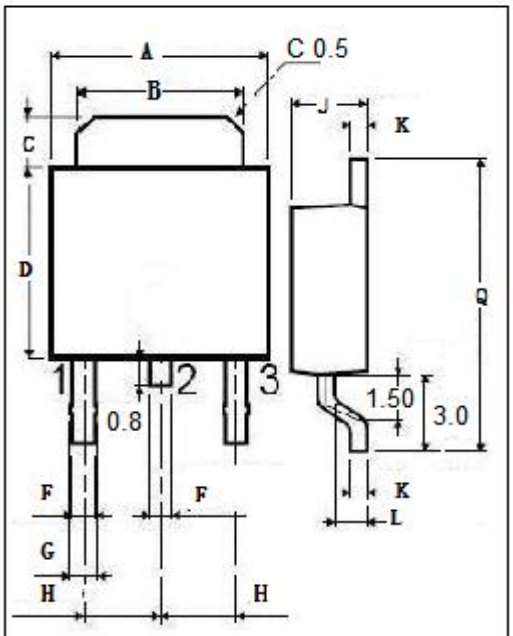
- Designed for use in switch mode power supplies and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage-Continuous	±30	V
I_D	Drain Current-Continuous	10	A
I_{DM}	Drain Current-Single Pluse	40	A
P_D	Total Dissipation @T_C=25℃	85	W
T_J	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.46	℃/W



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 1mA	200		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 1mA	3.25	5.25	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 5A		182	mΩ
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±30V;V_{DS}= 0		±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 200V; V_{GS}= 0		10	μA
V_{SD}	Forward On-Voltage	I_S= 10A; V_{GS}= 0		1.5	V